NSN 5962-01-353-3062

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View Online at https://aerobasegroup.com/nsn/5962-01-353-3062

| Body Length: |
|--|
| 1.060 inches |
| Body Width: |
| Between 0.220 inches and 0.310 inches |
| Body Height: |
| 0.185 inches |
| Maximum Power Dissipation Rating: |
| 2.0 watts |
| Operating Tempurature Range: |
| -55.0/+125.0 degrees celsius |
| Storage Tempurature Range: |
| -65.0/+150.0 degrees celsius |
| Features Provided: |
| Hermetically sealed and burn in and monolithic and bipolar |
| Inclosure Material: |
| Ceramic |
| Inclosure Configuration: |
| Dual-in-line |
| Output Logic Form: |
| Transistor-transistor logic |
| Input Circuit Pattern: |
| 16 input |
| Case Outline Source And Designator: |
| D-8 mil-m-38510 |
| Current Rating Per Characteristic: |
| 180.00 milliamperes reverse current, dc absolute |
| Terminal Surface Treatment: |
| Solder |
| Product Name: |
| And-or invert gate array |
| Voltage Rating And Type Per Characteristic: |
| -0.5 volts power source and 12.0 volts power source |
| Time Rating Per Chacteristic: |
| 30.00 nanoseconds delay |
| Memory Device Type: |
| Pal |
| Test Data Document: |
| 96906-mil-std-883 standard (includes industry or association standards, individual manufactureer standards, etc.). |
| Terminal Type And Quantity: |
| 20 printed circuit |
| Shelf Life: |

N/a

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|--|--|--|------|--|
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Demilitarization:

Yes - demil/mli

Fiig:

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